

Ordering number : ENN2246B

PNP/NPN Epitaxial Planar Silicon Transistors

**2SB1274/2SD1913****60V/3A Low-Frequency  
Power Amplifier Applications****Applications**

- General power amplifier.

**Features**

- Wide ASO (Adoption of MBIT process).
- Low saturation voltage.
- High reliability.
- High breakdown voltage.
- Micaless package facilitating mounting.

**Specifications**

():2SB1274

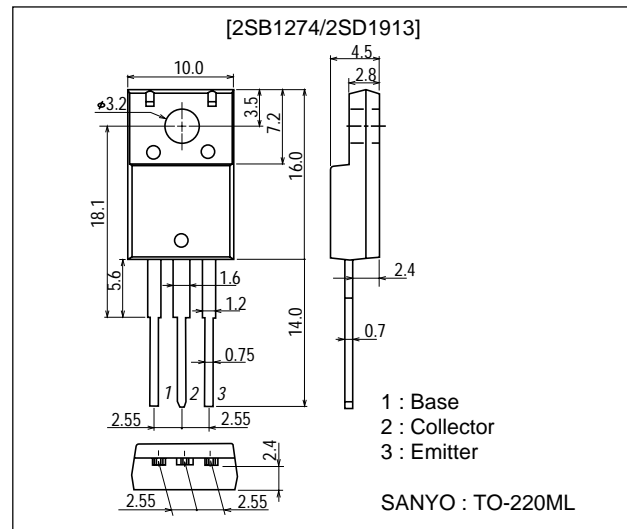
**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CB0</sub>		(-)60	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		(-)60	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)6	V
Collector Current	I <sub>C</sub>		(-)3	A
Collector Current (Pulse)	I <sub>CP</sub>		(-)8	A
Collector Dissipation	P <sub>C</sub>		2	W
		T <sub>c</sub> =25°C	20	W
Junction Temperature	T <sub>J</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(-)100	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(-)100	μA

Continued on next page.

**Package Dimensions**unit : mm  
2041A

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D2000 TS IM 8-2055 No.2246-1/4

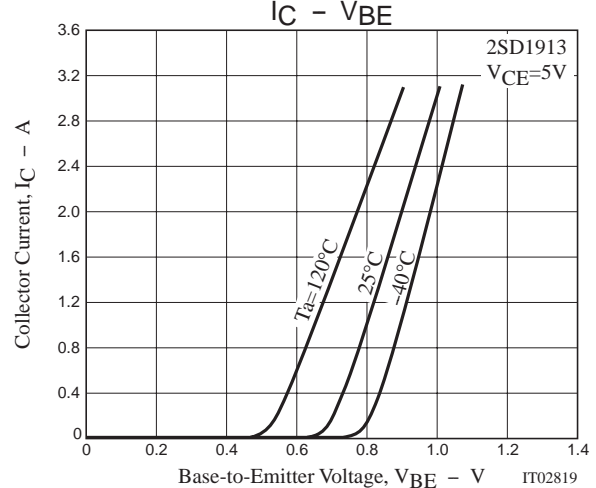
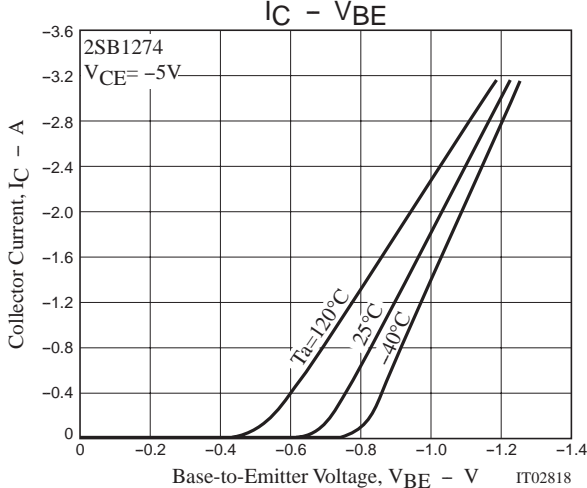
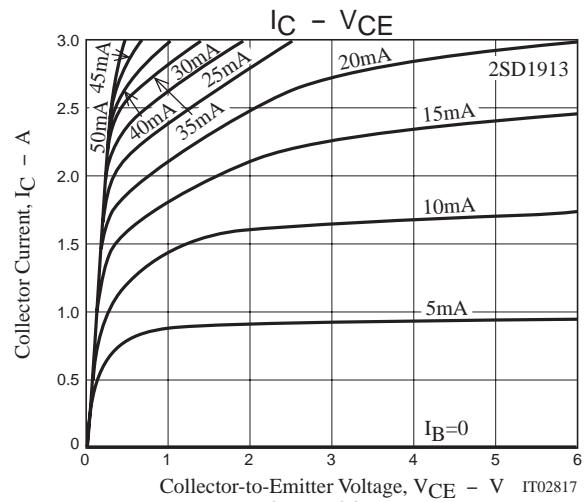
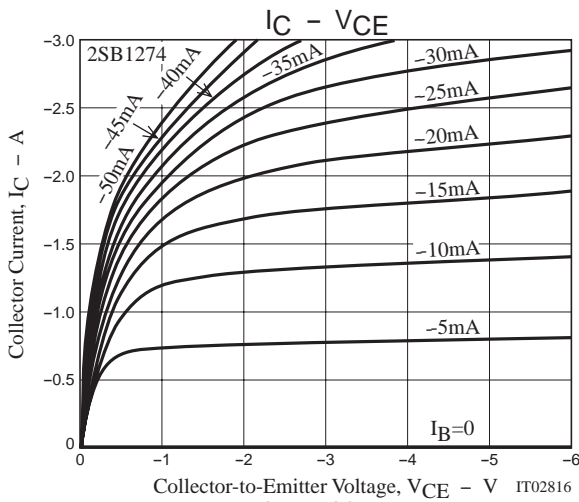
## 2SB1274/2SD1913

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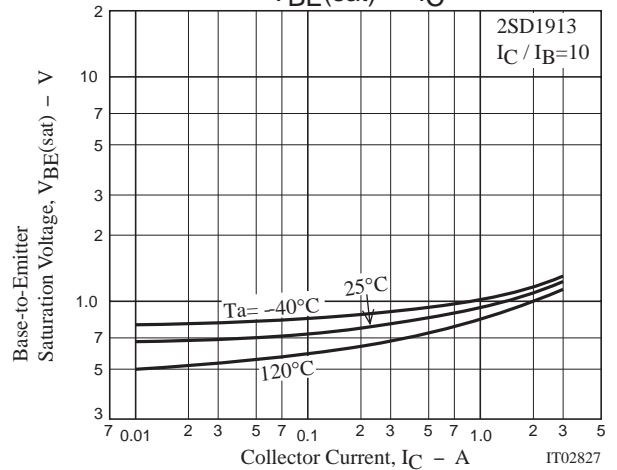
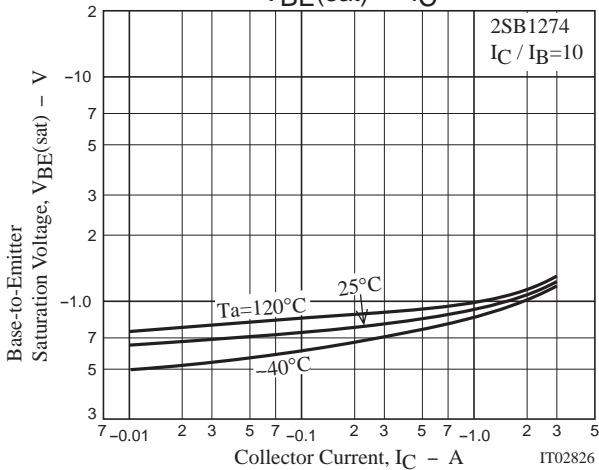
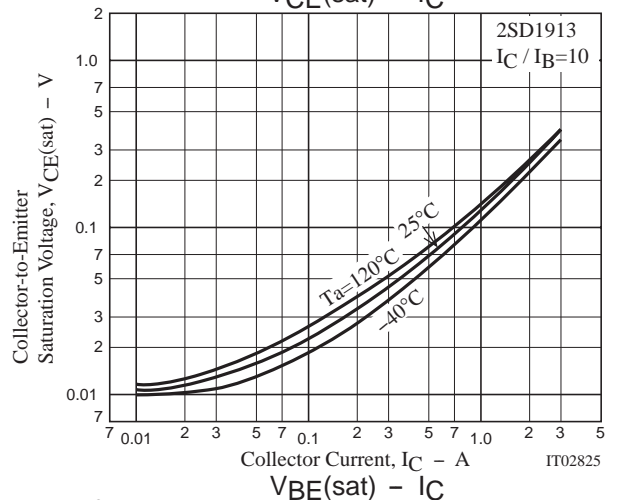
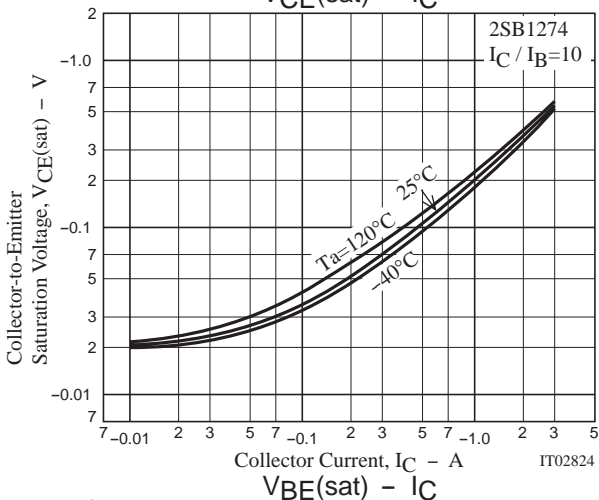
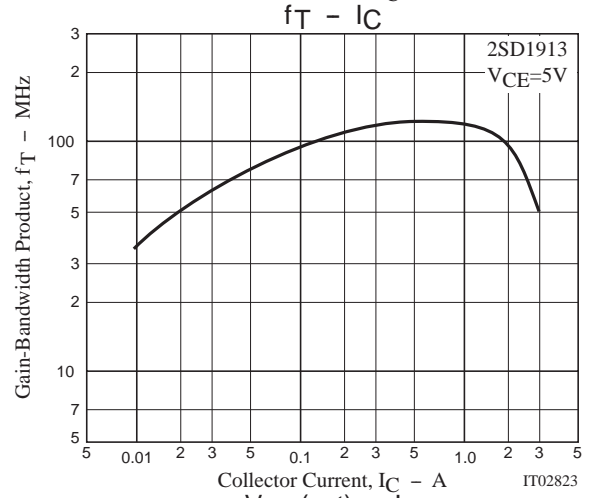
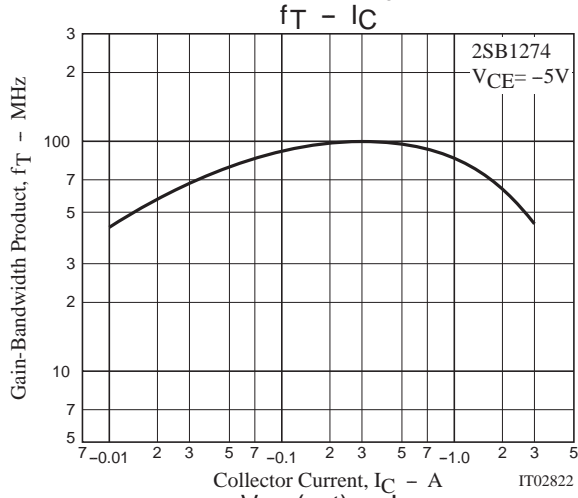
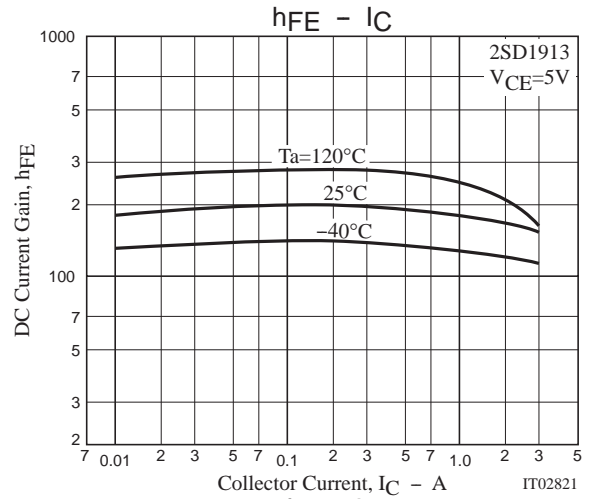
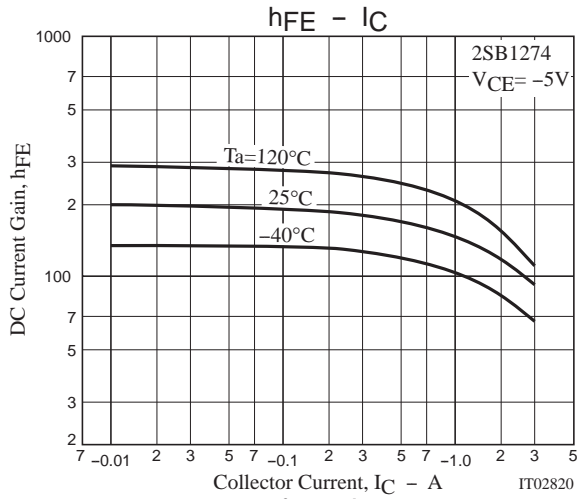
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
DC Current Gain	$h_{FE1}$	$V_{CE}=(-)5V, I_C=(-)0.5A$	70*		280*	
	$h_{FE2}$	$V_{CE}=(-)5V, I_C=(-)3A$	20			
Gain-Bandwidth Product	$f_T$	$V_{CE}=(-)5V, I_C=(-)0.5A$		100		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=(-)10V, f=1MHz$		(60)40		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)2A, I_B=(-)0.2A$		(-)0.4	(-)1	V
Base-to-Emitter Voltage	$V_{BE}$	$V_{CE}=(-)5V, I_C=(-)0.5A$		(-)0.8	(-)1	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)1mA, I_E=0$	(-)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	(-)60			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)1mA, I_C=0$	(-)6			V

\* : The 2SBB1274 / 2SD1913 are classified by 0.5A  $h_{FE}$  as follows :

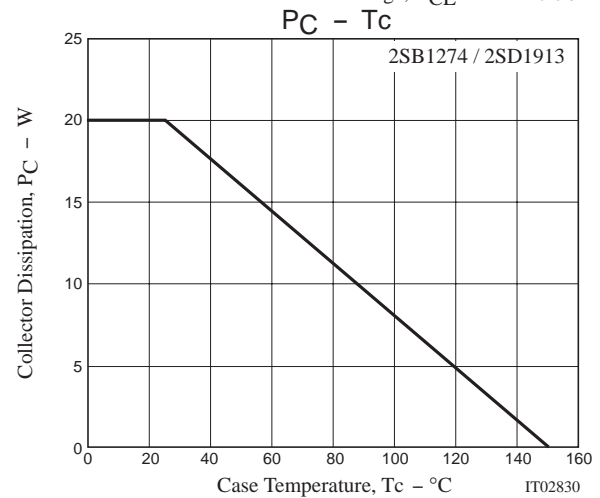
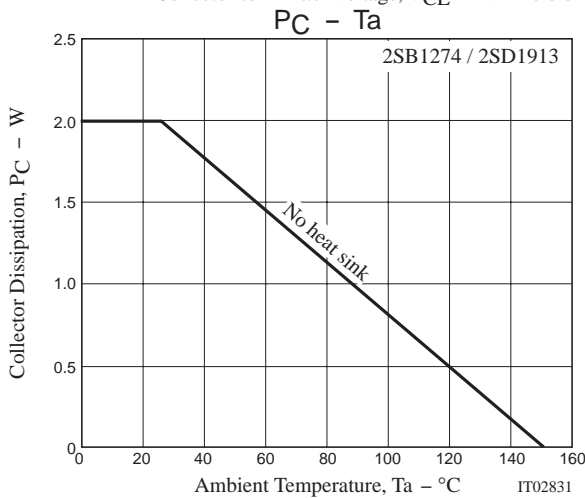
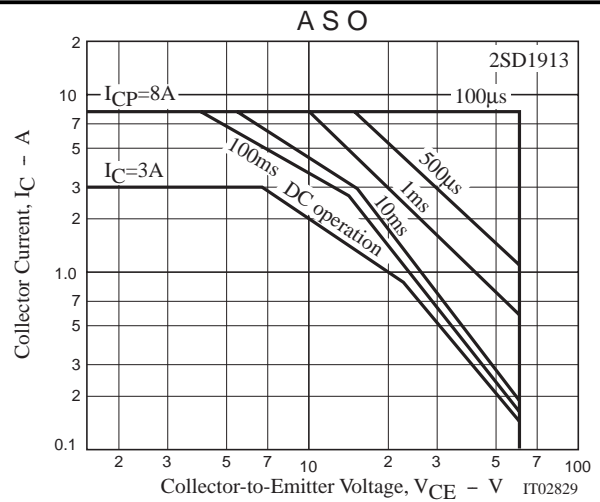
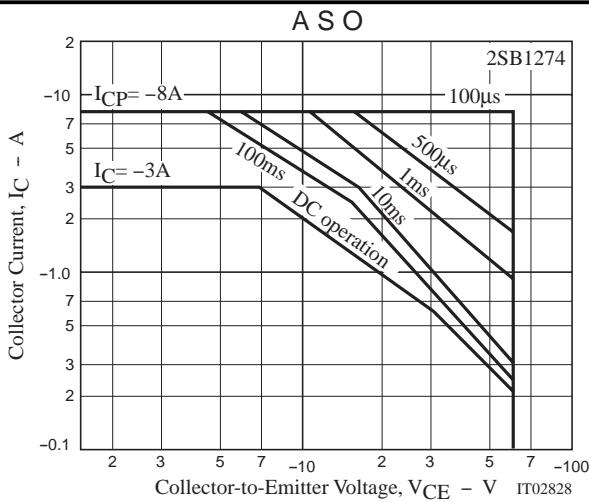
Rank	Q	R	S
$h_{FE}$	70 to 140	100 to 200	140 to 280



### 2SB1274/2SD1913



## 2SB1274/2SD1913



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